

REPORT DOCUMENTATION PAGE				Form Approved OMB NO. 0704-0188	
The public reporting burden for this collection of information is estimated to average 1 hour per response, including the time for reviewing instructions, searching existing data sources, gathering and maintaining the data needed, and completing and reviewing the collection of information. Send comments regarding this burden estimate or any other aspect of this collection of information, including suggestions for reducing this burden, to Washington Headquarters Services, Directorate for Information Operations and Reports, 1215 Jefferson Davis Highway, Suite 1204, Arlington VA, 22202-4302. Respondents should be aware that notwithstanding any other provision of law, no person shall be subject to any penalty for failing to comply with a collection of information if it does not display a currently valid OMB control number. PLEASE DO NOT RETURN YOUR FORM TO THE ABOVE ADDRESS.					
1. REPORT DATE (DD-MM-YYYY) 01-08-2012		2. REPORT TYPE Final Report		3. DATES COVERED (From - To) 2-Aug-2010 - 1-Feb-2012	
4. TITLE AND SUBTITLE Cryogenic Optoelectronic Probe Station				5a. CONTRACT NUMBER W911NF-10-1-0332	
				5b. GRANT NUMBER	
				5c. PROGRAM ELEMENT NUMBER 611103	
6. AUTHORS Cun-Zheng Ning				5d. PROJECT NUMBER	
				5e. TASK NUMBER	
				5f. WORK UNIT NUMBER	
7. PERFORMING ORGANIZATION NAMES AND ADDRESSES Arizona State University Office of Research & Sponsored Projects Administration Arizona State University Tempe, AZ 85287 -3503				8. PERFORMING ORGANIZATION REPORT NUMBER	
9. SPONSORING/MONITORING AGENCY NAME(S) AND ADDRESS(ES) U.S. Army Research Office P.O. Box 12211 Research Triangle Park, NC 27709-2211				10. SPONSOR/MONITOR'S ACRONYM(S) ARO	
				11. SPONSOR/MONITOR'S REPORT NUMBER(S) 57534-EL-RIP.1	
12. DISTRIBUTION AVAILABILITY STATEMENT Approved for Public Release; Distribution Unlimited					
13. SUPPLEMENTARY NOTES The views, opinions and/or findings contained in this report are those of the author(s) and should not be construed as an official Department of the Army position, policy or decision, unless so designated by other documentation.					
14. ABSTRACT The DURIP funding was used for the acquisition of a cryogenic optoelectronic probe station (COPS). The system has been installed and fully functional as expected. Various combinations with other existing setups have been tried. Successful experimental results using the COPS system have been obtained.					
15. SUBJECT TERMS Optoelectronics, Nanophotonics, Probe station					
16. SECURITY CLASSIFICATION OF:			17. LIMITATION OF ABSTRACT UU	15. NUMBER OF PAGES	19a. NAME OF RESPONSIBLE PERSON Cun-Zheng Ning
a. REPORT UU	b. ABSTRACT UU	c. THIS PAGE UU			19b. TELEPHONE NUMBER 480-965-7421

Report Title

Cryogenic Optoelectronic Probe Station

ABSTRACT

The DURIP funding was used for the acquisition of a cryogenic optoelectronic probe station (COPS). The system has been installed and fully functional as expected. Various combinations with other existing setups have been tried. Successful experimental results using the COPS system have been obtained.

Enter List of papers submitted or published that acknowledge ARO support from the start of the project to the date of this printing. List the papers, including journal references, in the following categories:

(a) Papers published in peer-reviewed journals (N/A for none)

Received

Paper

TOTAL:

Number of Papers published in peer-reviewed journals:

(b) Papers published in non-peer-reviewed journals (N/A for none)

Received

Paper

TOTAL:

Number of Papers published in non peer-reviewed journals:

(c) Presentations

Number of Presentations: 0.00

Non Peer-Reviewed Conference Proceeding publications (other than abstracts):

Received

Paper

TOTAL:

Number of Non Peer-Reviewed Conference Proceeding publications (other than abstracts):

Peer-Reviewed Conference Proceeding publications (other than abstracts):

Received

Paper

TOTAL:

Number of Peer-Reviewed Conference Proceeding publications (other than abstracts):

(d) Manuscripts

Received

Paper

TOTAL:

Number of Manuscripts:

Books

Received

Paper

TOTAL:

Patents Submitted

Patents Awarded

Awards

Graduate Students

<u>NAME</u>	<u>PERCENT SUPPORTED</u>
FTE Equivalent:	
Total Number:	

Names of Post Doctorates

<u>NAME</u>	<u>PERCENT SUPPORTED</u>
FTE Equivalent:	
Total Number:	

Names of Faculty Supported

<u>NAME</u>	<u>PERCENT SUPPORTED</u>
FTE Equivalent:	
Total Number:	

Names of Under Graduate students supported

<u>NAME</u>	<u>PERCENT SUPPORTED</u>
FTE Equivalent:	
Total Number:	

Student Metrics

This section only applies to graduating undergraduates supported by this agreement in this reporting period

The number of undergraduates funded by this agreement who graduated during this period: 0.00

The number of undergraduates funded by this agreement who graduated during this period with a degree in science, mathematics, engineering, or technology fields:..... 0.00

The number of undergraduates funded by your agreement who graduated during this period and will continue to pursue a graduate or Ph.D. degree in science, mathematics, engineering, or technology fields:..... 0.00

Number of graduating undergraduates who achieved a 3.5 GPA to 4.0 (4.0 max scale): 0.00

Number of graduating undergraduates funded by a DoD funded Center of Excellence grant for Education, Research and Engineering:..... 0.00

The number of undergraduates funded by your agreement who graduated during this period and intend to work for the Department of Defense 0.00

The number of undergraduates funded by your agreement who graduated during this period and will receive scholarships or fellowships for further studies in science, mathematics, engineering or technology fields: 0.00

Names of Personnel receiving masters degrees

NAME

Total Number:

Names of personnel receiving PhDs

NAME

Total Number:

Names of other research staff

NAME

PERCENT SUPPORTED

FTE Equivalent:

Total Number:

Sub Contractors (DD882)

Inventions (DD882)

Scientific Progress

Technology Transfer

Cryogenic Optoelectronic Probe Station (COPS) System: Final Report

The DURIP funding was used for the acquisition of a cryogenic optoelectronic probe station (COPS). The system has been installed and fully functioning as expected. Various combinations with other existing setups have been tried. Successful experimental results using the COPS system have been obtained.

Basic Capability

Our cryogenic optoelectronic probe station (Lake Shore, model TTPX) is capable of measurement in a wide temperature range from 4.5K to 475K. Unlike most other COPS which only have four probe arms, our COPS consists of six probe arms. All of the probe arms are ultra-stable, micromanipulated, each providing precise 3-axis probe position control to land the probe tip accurately on device features. Four of the arms are equipped with electrical probes which not only can be used for electrical injection but also capable of doing a standard four-point probe measurement to determine electrical



Fig.1 TTPX cryogenic optoelectronic probe station

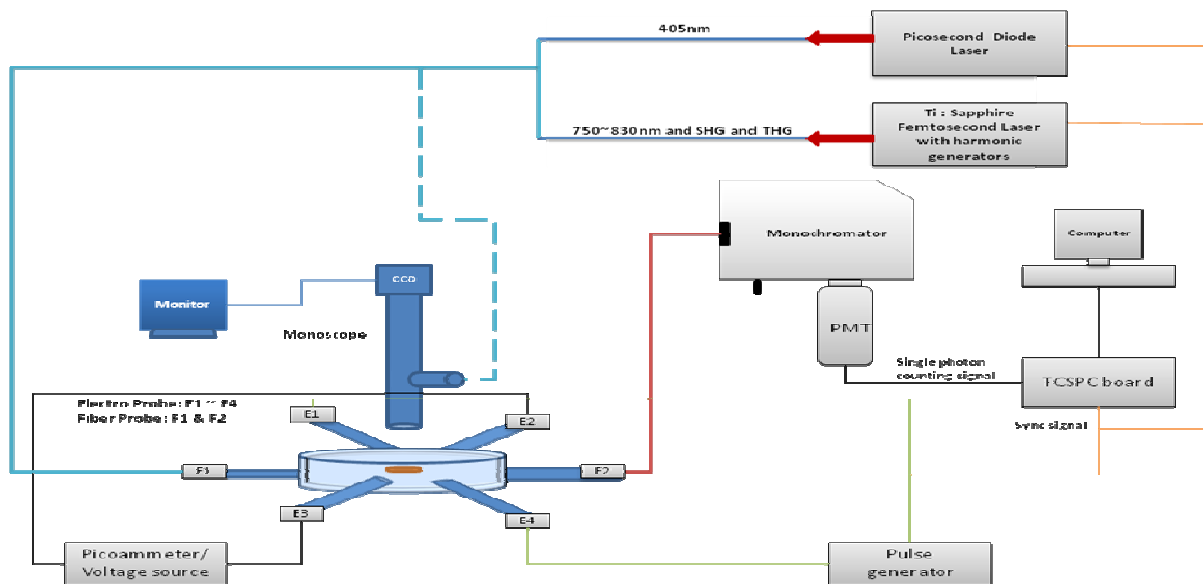


Fig.2 Schematic setup of COPS in conjunction with other instrument for time-integrated and time-resolved optical measurements with varying temperature capability and for two dimensional scanning

transport properties such as conductivity and I-V curve. All of the probes can be used for low-noise, high-impedance electrical measurements. Additionally, the other two arms are

configured as fiber probes, which could be used for laser excitation and collection of emitted light (e.g., PL or lasing). The Edmund 16X precision zoom lens system working with a Mitutoyo objective allows a 2- μm spatial resolution while still maintain a large working distance. The OPTTEM 70XL zoom system allows a NIR observation. Our COPS is also fully compatible with other existing lasers and detectors so that the overall capability of our lab is now greatly expanded. As an example, Fig.2 shows schematic of integrating the COPS with other existing time-resolved or time-integrated photoluminescence measurements to obtained time or spectral resolved two dimensional scanning measurements. All these unique features make our COPS a powerful tool for a variety of nanophotonics characterization. Such capability is very important for a few on-going projects under DOD support.

Selected Examples of Research Using COPS

Example 1: sheet resistance measurement using four-point probe

We have fabricated some Indium doped ZnS thin film for an N type contact material. In order to figure out the effective donor

concentration of this thin film contact material, we need to know the sheet resistance. As shown in Fig. 1, four electric probes are landed onto the surface of the thin film at an equal distance of 5 mm. When 10 V is applied between probe 1 and 4, we get a current of 80.4 nA and a voltage of 62.4 mV across probe 2 and 3. Therefore we can determine the sheet resistance by using Eq:

$R_{sheet} = \frac{\pi}{\ln(2)} \frac{V_{23}}{I}$. This gives the sheet resistance of 3.52 $\text{M}\Omega/\square$ and indicated that the effective donor concentration is around 10^{16} cm^{-3} .

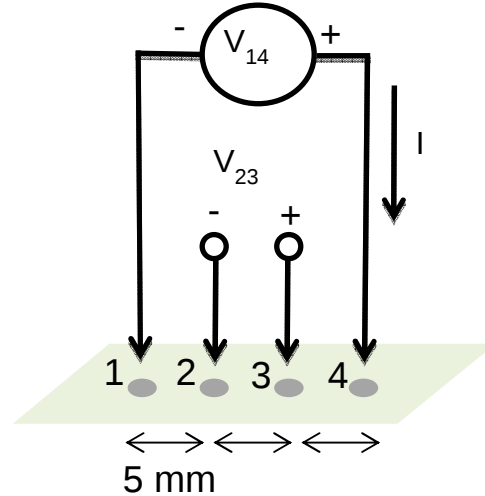


Figure 3 Four-point probe configuration for sheet resistance measurement.

Example 2: Electroluminescence and I-V curve measurement of nanolaser device under low temperature

One of great advantages of COPS is that it allows us to perform electrical injection luminescence or lasing study of nanowires and nanopillars without complicated fabrication processes. As an example, we use COPS to measure the I-V curve of fabricated nanolaser devices before wire bonding. Due to the difficulty of doing wire bonding and the possibility of causing damage to the nanolaser device, COPS provides us a quick and safe fashion of testing the IV property of the devices. With the optical probe, we can even collect the EL signal of the device. Fig. 4(a) shows a nanolaser device under

test. The device is forward biased under two electric probes. One optical probe on top of the device collects the emission light and then coupled to a spectrometer. The entire system is cooled down to 78 K. Fig. 2(b) shows the corresponding IV curve and emission intensity at different injection current. A clear lasing behavior can be observed with a lasing threshold around 400 μA .

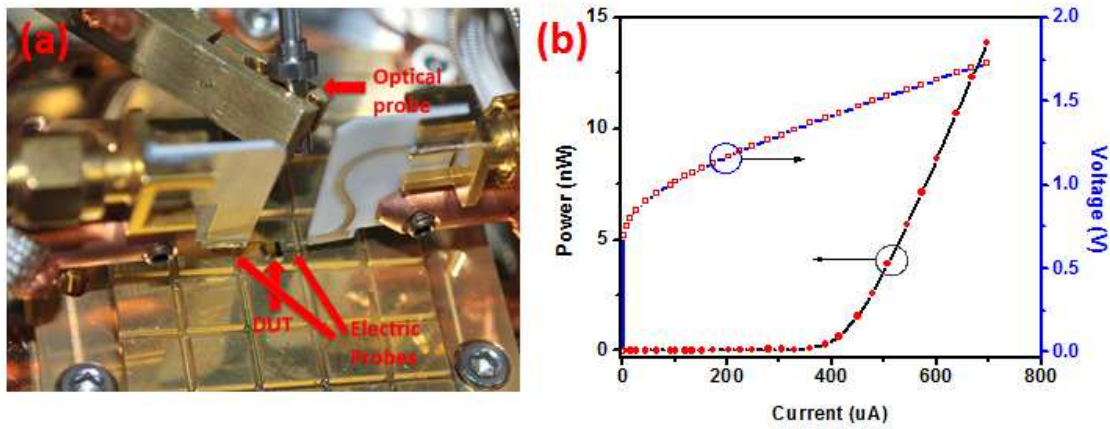


Figure 4 (a) A nanolaser device under test (DUT). (b) I-V curve and emission power under different injection current.